

# 60V N-Channel Power MOSFET

**TSM60N06** 



TO-252 (DPAK)



#### Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
60	7.3 @ V <sub>GS</sub> =10V	66

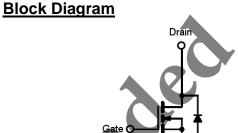
#### **Features**

- Advanced Trench Technology
- Low  $R_{DS(ON)}$  7.3m $\Omega$  (Max.)
- Low gate charge typical @ 81nC (Typ.)
- Low Crss typical @ 339pF (Typ.)

### **Ordering Information**

Part No.	Package	Packing
TSM60N06CP ROG	TO-252	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product



N-Channel MOSFET

### Absolute Maximum Rating (T<sub>C</sub> = 25°C unless otherwise noted

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	60	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
	T <sub>C</sub> = 25°C		66		
Continuous Drain Current	$T_C = 70^{\circ}C$		53	٨	
Continuous Diam Current	$T_A = 25^{\circ}C$	l <sub>D</sub>	13	Α	
	T <sub>A</sub> = 70°C		10		
Drain Current-Pulsed Note 1		$I_{DM}$	150	Α	
Avalanche Current, L = 0.1mH		$I_{AS}$ , $I_{AR}$	53	Α	
Avalanche Energy, L = 0.1mH		$E_{AS},E_{AR}$	400	mJ	
	$T_C = 25^{\circ}C$		44.6		
Maximum Dawar Dischartion	$T_C = 70^{\circ}C$	28.6		\\/	
Maximum Power Dissipation	$T_A = 25^{\circ}C$	P <sub>D</sub>	2	W	
<u> </u>	$T_A = 70^{\circ}C$		1.3		
Storage Temperature Range		$T_{STG}$	-55 to +150	$^{\circ}$	
Operating Junction Temperature Range		TJ	-55 to +150	°C	

<sup>\*</sup> Limited by maximum junction temperature

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R <sub>eJC</sub>	2.8	°C/W
Thermal Resistance - Junction to Ambient	R <sub>OJA</sub>	62	°C/W

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### **Electrical Specifications** (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	60			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 30A$	R <sub>DS(ON)</sub>		6.3	7.3	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 48V, V_{GS} = 0V$	I <sub>DSS</sub>			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Dynamic						
Total Gate Charge	\/ 00\/ L 00A	$Q_g$		81	<b>-</b>	
Gate-Source Charge	$V_{DS} = 30V, I_{D} = 30A,$	$Q_{gs}$		23		nC
Gate-Drain Charge	$V_{GS} = 10V$	$Q_{gd}$	(	24		
Input Capacitance	.,	C <sub>iss</sub>		4382		
Output Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$	C <sub>oss</sub>		668		рF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>	7	339		
Switching						
Turn-On Delay Time		t <sub>d(on)</sub>		25		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 30V,$	t <sub>r</sub>		19		. 0
Turn-Off Delay Time	$R_G = 3.3\Omega$ , $I_D = 30A$	t <sub>d(off)</sub>		85		nS
Turn-Off Fall Time		t <sub>f</sub>		43		
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	$V_{GS} = 0V$ , $I_{S} = 20A$	V <sub>SD</sub>	-	0.8	1.3	V
Reverse Recovery Time	I <sub>S</sub> = 30A, T <sub>J</sub> = 25 °C	t <sub>fr</sub>		36		nS
Reverse Recovery Charge	dl/dt = 100A/us	Q <sub>fr</sub>		53		nC

#### Notes:

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Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design. R<sub>θJA</sub> shown below for single device operation on FR-4 in still air

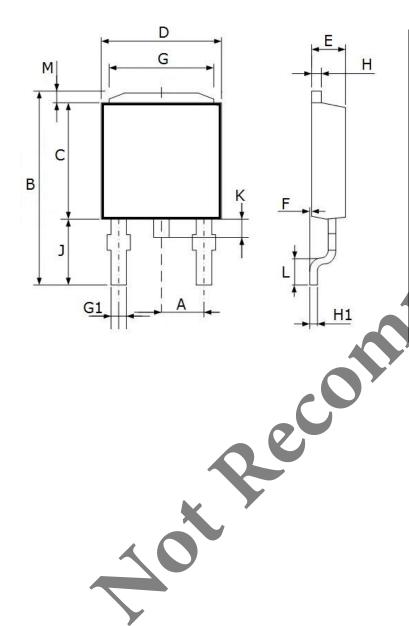


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# **TO-252 Mechanical Drawing**



TO-252 DIMENSION						
DIM	MILLIMETERS		INCHES			
DIIVI	MIN	MAX	MIN	MAX		
Α	2.286	BSC	0.090	BSC		
В	9.40	10.40	0.370	0.409		
С	5.40	6.23	0.213	0.245		
D	6.40	6.80	0.252	0.268		
Е	2.20	2.40	0.087	0.094		
F	0.00	0.20	0.000	0.008		
G	5.20	5.50	0.205	0.217		
G1	0.50	0.91	0.020	0.036		
Н	0.45	0.60	0.018	0.024		
H1	0.40	0.60	0.016	0.024		
7	2.50	2.90	0.098	0.114		
K	0.60	1.00	0.023	0.039		
	1.40	1.78	0.055	0.070		
M	0.88	1.28	0.034	0.050		

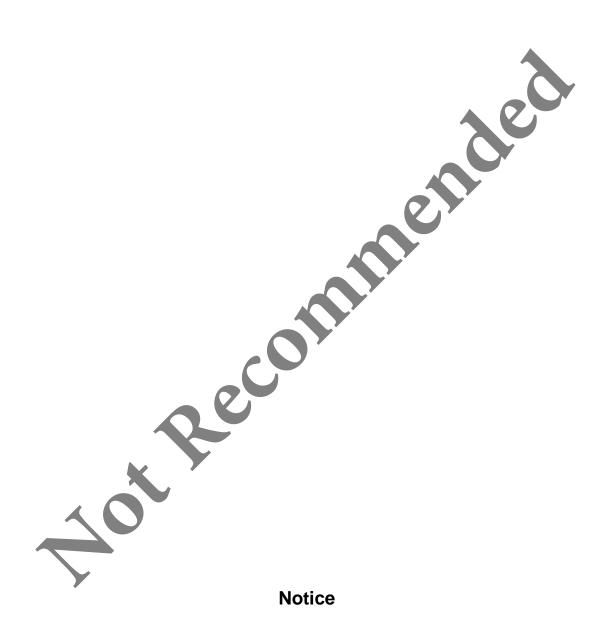
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